

REMARKS

Claim 1 calls for a phase change memory element. In the specification, it is explained that a memory cell may include a memory element 22 and a select device 14. See page 2, lines 19 and 20. Likewise, in the cited Lowrey reference, there is a reference to memory cells 111-119 wherein the memory cells each include a select device 120 and a memory element 130. See paragraph 27. Thus, there is a clear distinguishing between a memory element and a select device.

Moreover, in the cited Lowrey reference, it is explained in paragraph 33 that "Unlike a phase change memory element, the switching material of select device 20 may not change phase."

Thus, Lowrey uses the exact same language used in the present application claims to distinguish between what is called a phase change memory element and a select device (that does not change phase). It is explained that there is no such thing as a phase change select device because the select device does not change phase. Thus, the memory element must include the storage device of a phase change memory cell and a "phase change" memory element must change phase, which precludes reading the claim on a select device including the select device of the type that includes a chalcogenide material, as explained in paragraph 33 of the cited Lowrey reference.

Therefore, reconsideration is respectfully requested.

Respectfully submitted,



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